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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Re the Application of: **Masaki KURASAWA et al.**

Group Art Unit: **2814**

Serial No.: **09/960,398**

Examiner: **T. LE**

Filed: **September 24, 2001**

P.T.O. Confirmation No.: **5650**

For. **CAPACITOR AND METHOD FOR FABRICATING THE SAME, AND
SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: July 11, 2003

Sir:

This is a Preliminary Amendment for the above-captioned patent application. Please amend
the above-captioned patent application as follows:

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IN THE CLAIMS:

Please amend claims 1, 3 and 14 as follows:

1. (Amended) A capacitor comprising:
- a buffer structure formed on a substrate;
 - a lower electrode formed on the buffer structure;
 - a capacitor dielectric film formed on the lower electrode, and formed of a perovskite ferroelectric material having a smaller thermal expansion coefficient than that of the buffer structure and having a crystal oriented substantially perpendicular to a surface of the lower electrode; and
 - an upper electrode formed on the capacitor dielectric film,

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